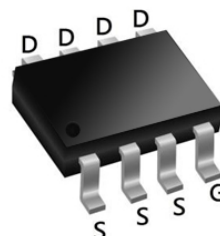


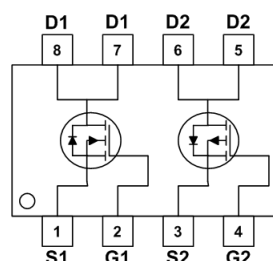
N-Ch and P-Ch Fast Switching MOSFETs

Features:

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology



SOP8 Pin Configuration



BVDSS	RDS(on)(Typ.)	ID
60V	38mΩ	5A
-60V	80mΩ	-3.8A

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	60	-60	V
V_{GS}	Gate-Source Voltage	±20	±20	V
$I_{D@T_A=25^{\circ}C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	5	-3.8	A
$I_{D@T_A=70^{\circ}C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	4	-3.2	A
I_{DM}	Pulsed Drain Current ²	20	-14	A
EAS	Single Pulse Avalanche Energy ³	22	28.8	mJ
I_{AS}	Avalanche Current	21	-24	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	2	2	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	85	°C/W
	Thermal Resistance Junction-Ambient ¹ (t≤10sec)	---	62.5	°C/W

N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5A	---	38	52	mΩ
		V _{GS} =4.5V, I _D =4A	---	55	75	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =48V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =4A	---	28	---	S
Q _g	Total Gate Charge (4.5V)	V _{DS} =48V, V _{GS} =4.5V, I _D =4A	---	19	---	nC
Q _{gs}	Gate-Source Charge		---	2.6	---	
Q _{gd}	Gate-Drain Charge		---	4.1	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =3.3Ω, I _D =4A	---	3	---	ns
T _r	Rise Time		---	34	---	
T _{d(off)}	Turn-Off Delay Time		---	23	---	
T _f	Fall Time		---	6	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	1027	---	pF
C _{oss}	Output Capacitance		---	65	---	
C _{rss}	Reverse Transfer Capacitance		---	46	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	2.5	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=21A
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-3.5A	---	80	100	mΩ
		V _{GS} =-4.5V , I _D =-3.1A	---	100	105	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-	---	-	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =-48V , V _{GS} =0V , T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V , I _D =-3A	---	8.5	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-48V , V _{GS} =-4.5V , I _D =-3A	---	12.	---	nC
Q _{gs}	Gate-Source Charge		---	2.2	---	
Q _{gd}	Gate-Drain Charge		---	6.3	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-15V , V _{GS} =-10V , R _G =3.3Ω , I _D =-1A	---	9.2	---	ns
T _r	Rise Time		---	20.	---	
T _{d(off)}	Turn-Off Delay Time		---	46.	---	
T _f	Fall Time		---	9.4	---	
C _{iss}	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz	---	113	---	pF
C _{oss}	Output Capacitance		---	76	---	
C _{rss}	Reverse Transfer Capacitance		---	50	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	-	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C	---	---	-	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-24A

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

N-Channel Typical Characteristics

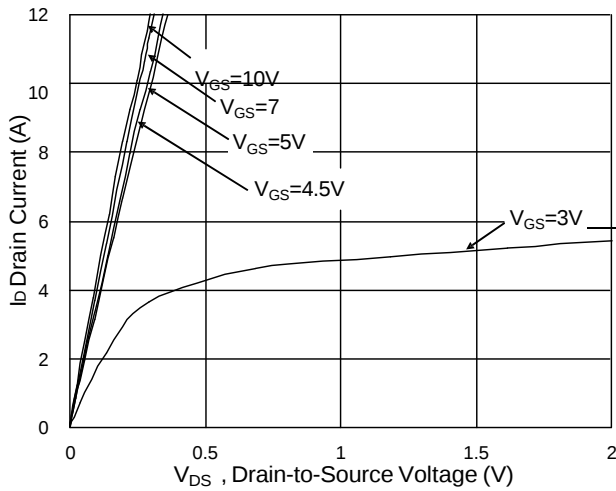


Fig.1 Typical Output Characteristics

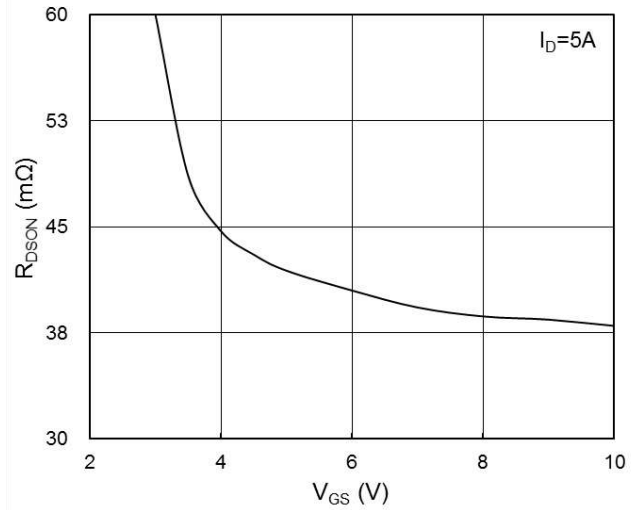


Fig.2 On-Resistance vs. G-S Voltage

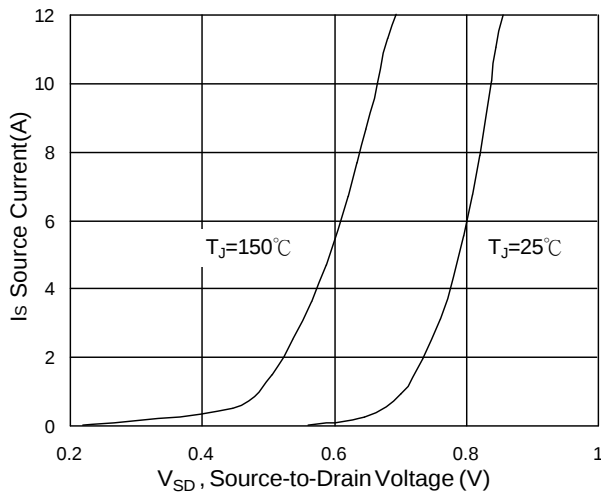


Fig.3 Source Drain Forward Characteristics

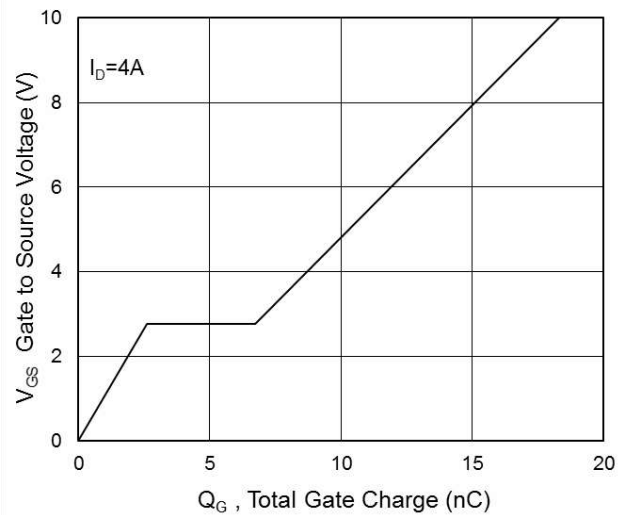


Fig.4 Gate-Charge Characteristics

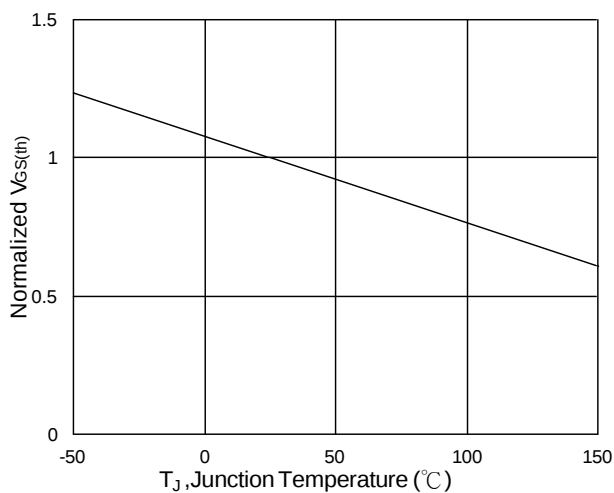


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

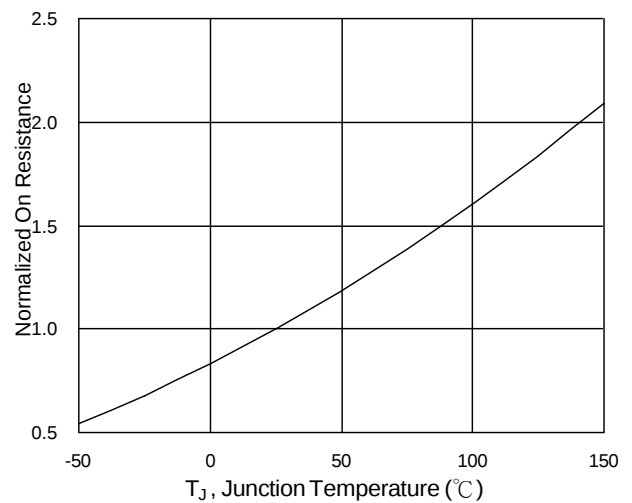


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

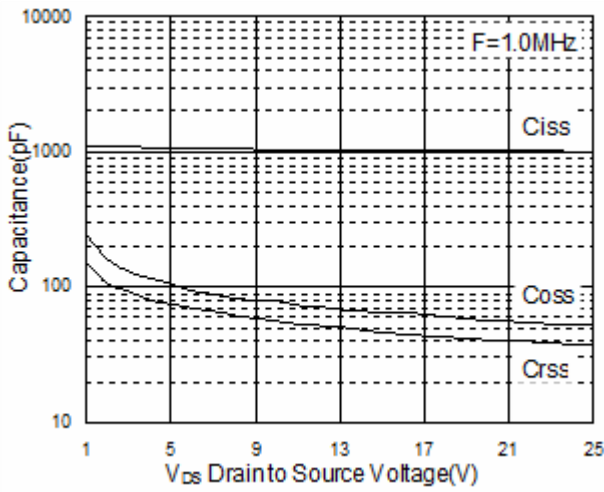


Fig.7 Capacitance

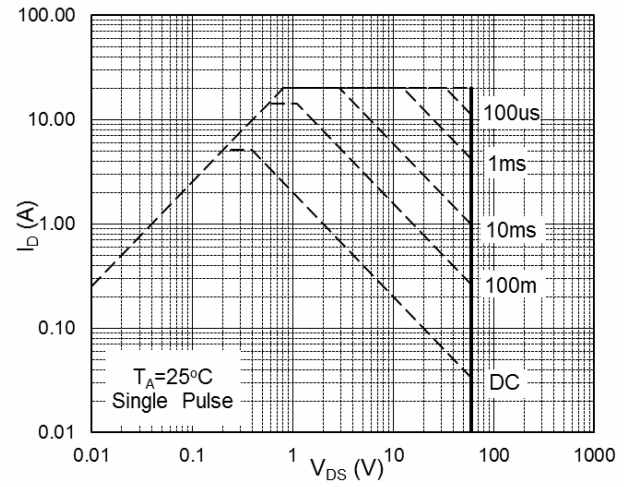


Fig.8 Safe Operating Area

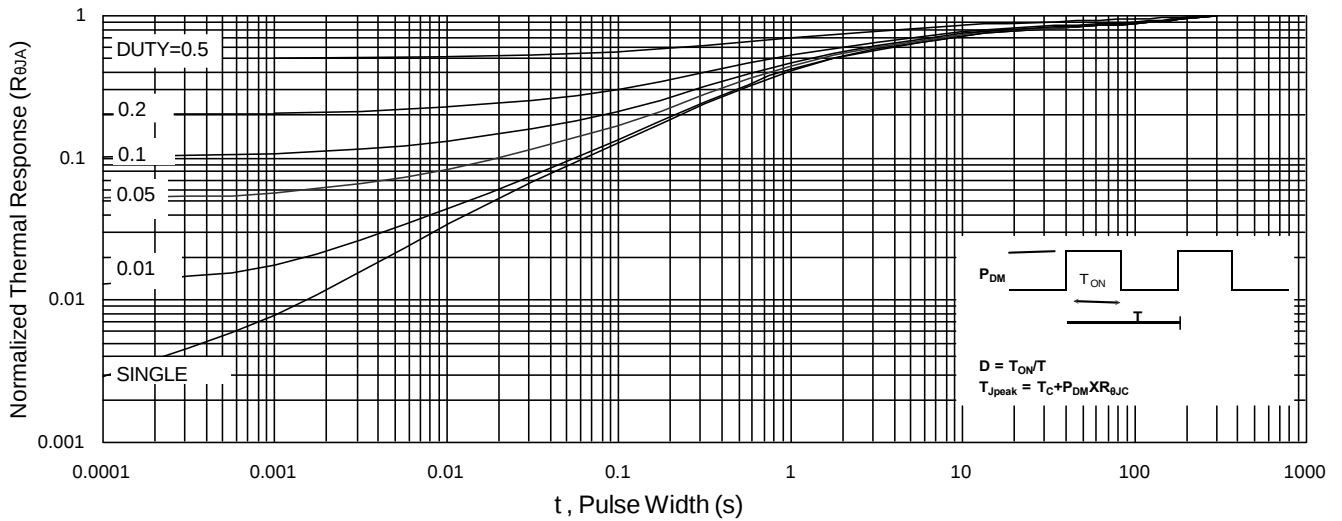


Fig.9 Normalized Maximum Transient Thermal Impedance

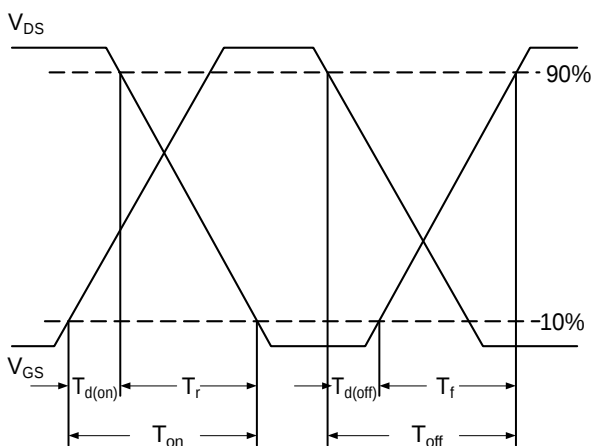
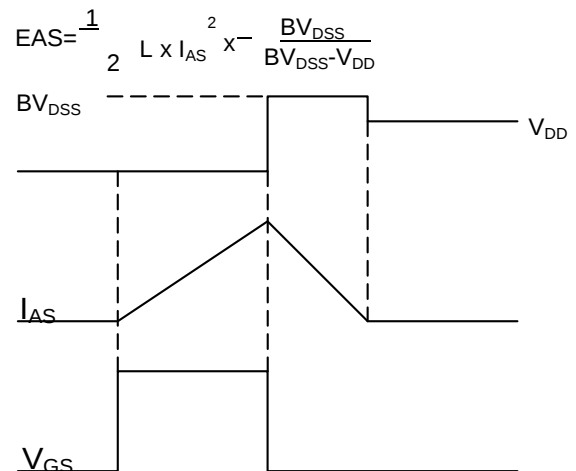


Fig.10 Switching Time Waveform



P-Channel Typical Characteristics

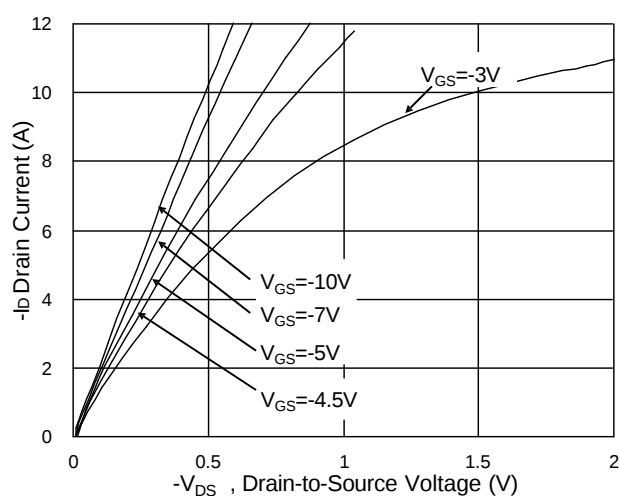


Fig.1 Typical Output Characteristics

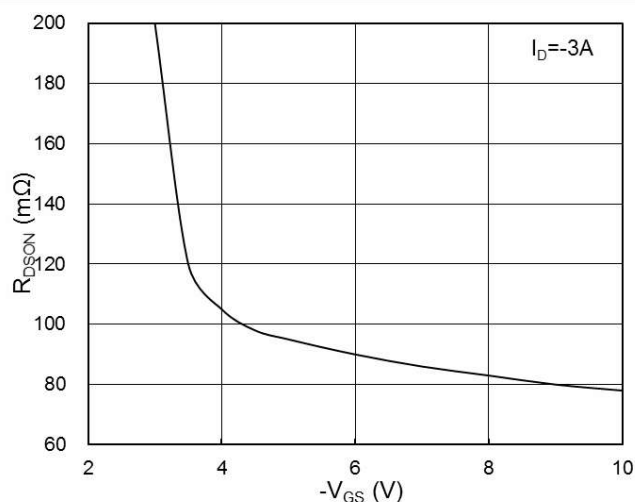


Fig.2 On-Resistance vs. G-S Voltage

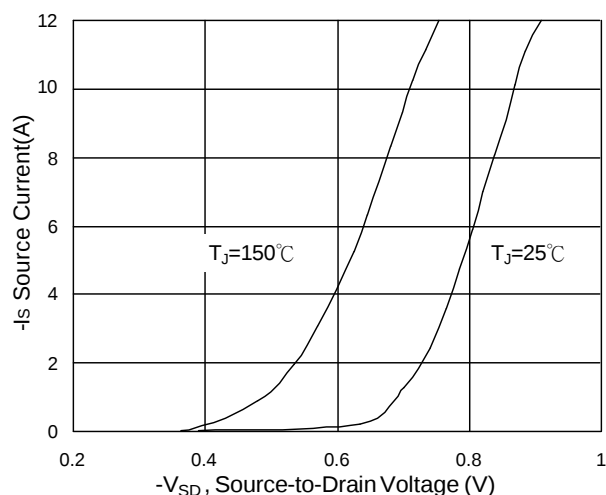


Fig.3 Source Drain Forward Characteristics

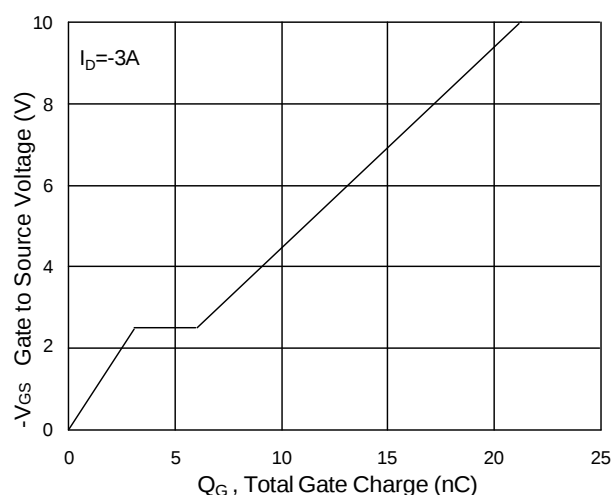


Fig.4 Gate-Charge Characteristics

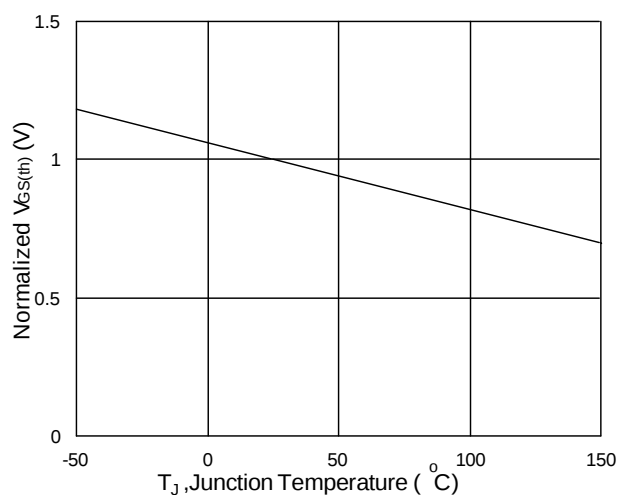


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

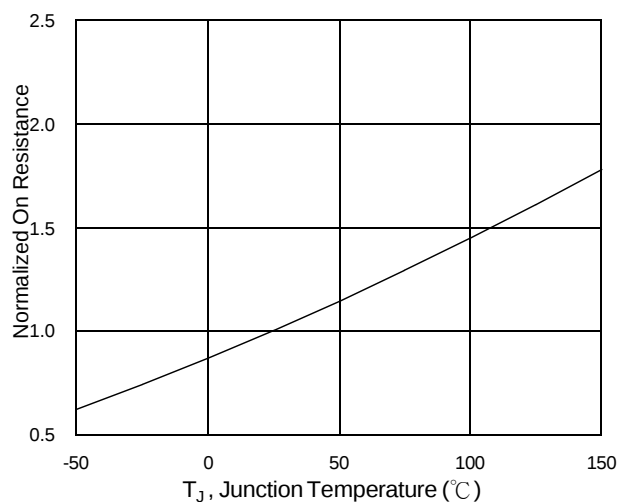


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

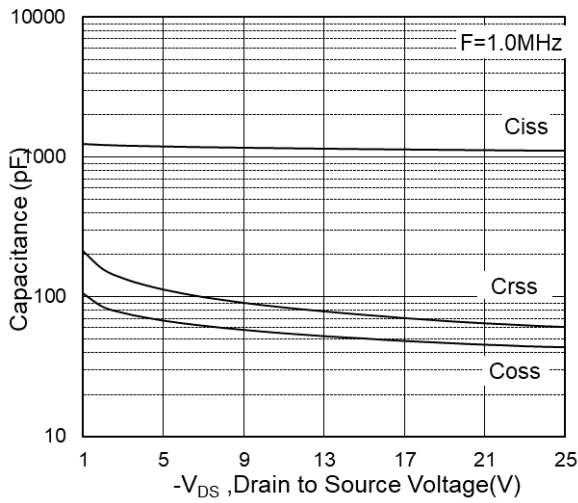


Fig.7 Capacitance

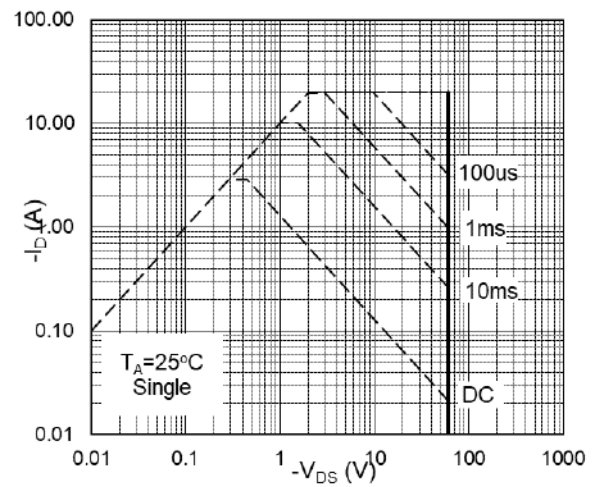


Fig.8 Safe Operating Area

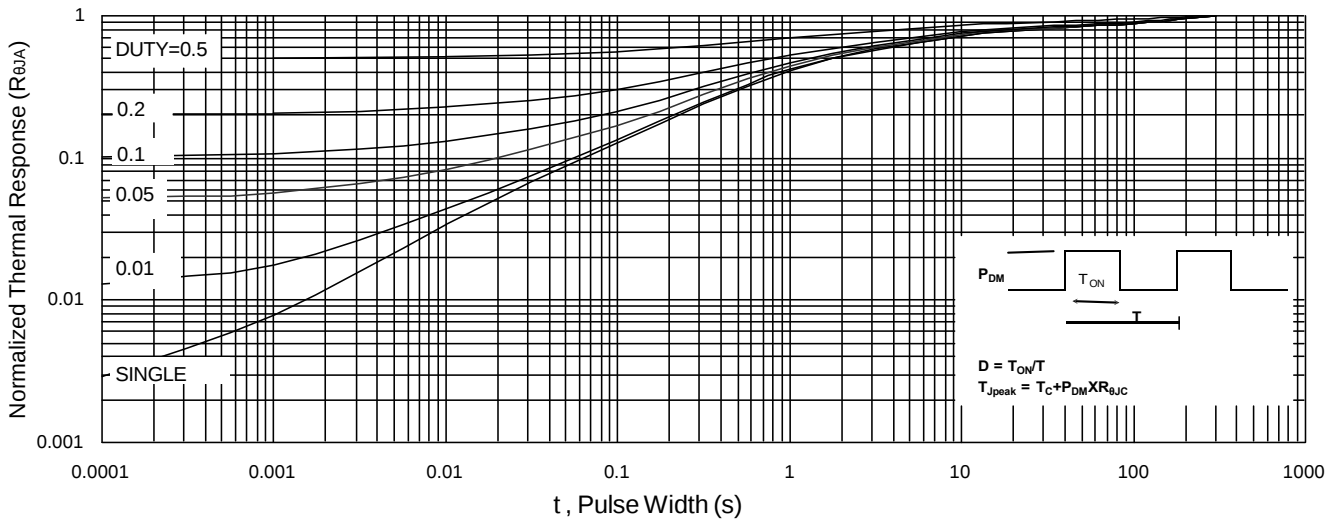


Fig.9 Normalized Maximum Transient Thermal Impedance

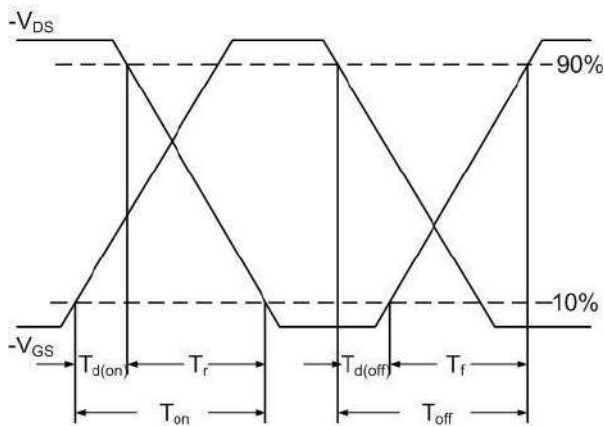


Fig.10 Switching Time Waveform

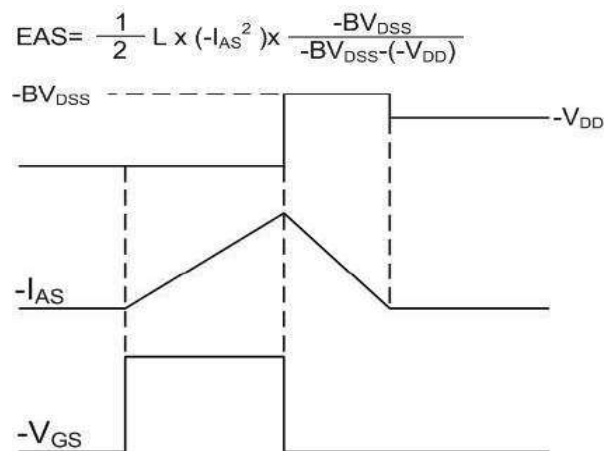


Fig.11 Unclamped Inductive Waveform